

# CM800DZ-34H

HIGH POWER SWITCHING USE  
INSULATED TYPE

3rd-Version HVIGBT (High Voltage Insulated Gate Bipolar Transistor) Modules

## CM800DZ-34H



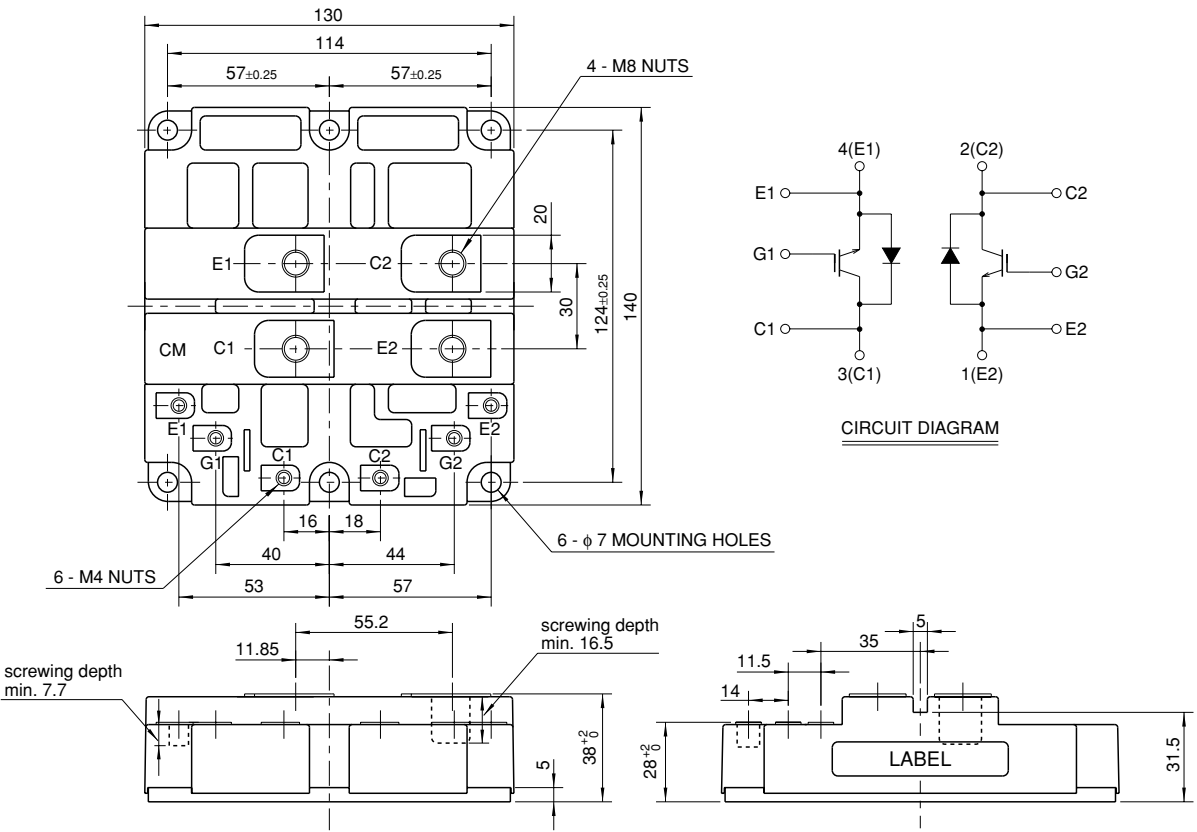
- IC .....800A
- VCES ..... 1700V
- Insulated Type
- 2-element in a Pack
- AISiC Baseplate

## APPLICATION

Traction drives, High Reliability Converters / Inverters, DC choppers

## OUTLINE DRAWING & CIRCUIT DIAGRAM

Dimensions in mm



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**MAXIMUM RATINGS**

| Symbol                   | Item                              | Conditions  | Ratings    | Unit |
|--------------------------|-----------------------------------|---|------------|------|
| V <sub>CE</sub> S        | Collector-emitter voltage         | V <sub>GE</sub> = 0V, T <sub>j</sub> = 25°C   | 1700       | V    |
| V <sub>GE</sub> S        | Gate-emitter voltage              | V <sub>CE</sub> = 0V, T <sub>j</sub> = 25°C   | ±20        | V    |
| I <sub>C</sub>           | Collector current                 | T <sub>C</sub> = 80°C   | 800        | A    |
| I <sub>CM</sub>          |                                   | Pulse (Note 1)  | 1600       | A    |
| I <sub>E</sub> (Note 2)  | Emitter current                   |   | 800        | A    |
| I <sub>EM</sub> (Note 2) |                                   | Pulse (Note 1)  | 1600       | A    |
| P <sub>C</sub> (Note 3)  | Maximum power dissipation         | T <sub>C</sub> = 25°C, IGBT part  | 6200       | W    |
| T <sub>j</sub>           | Junction temperature              |   | -40 ~ +150 | °C   |
| T <sub>op</sub>          | Operating temperature             |   | -40 ~ +125 | °C   |
| T <sub>stg</sub>         | Storage temperature               |   | -40 ~ +125 | °C   |
| V <sub>iso</sub>         | Isolation voltage                 | RMS, sinusoidal, f = 60Hz, t = 1min.  | 4000       | V    |
| t <sub>p</sub> sc        | Maximum short circuit pulse width | V <sub>CC</sub> = 1150V, V <sub>CE</sub> S ≤ 1700V, V <sub>GE</sub> = 15V<br>T <sub>j</sub> = 125°C | 10         | μs   |

**ELECTRICAL CHARACTERISTICS**

| Symbol                    | Item                                 | Conditions  | Limits |      |      | Unit     |
|---------------------------|--------------------------------------|---|--------|------|------|----------|
|                           |                                      |   | Min    | Typ  | Max  |          |
| I <sub>CES</sub>          | Collector cut-off current            | V <sub>CE</sub> = V <sub>CE</sub> S, V <sub>GE</sub> = 0V, T <sub>j</sub> = 25°C            | —      | —    | 12   | mA       |
| V <sub>GE(th)</sub>       | Gate-emitter threshold voltage       | I <sub>C</sub> = 80mA, V <sub>CE</sub> = 10V, T <sub>j</sub> = 25°C                         | 4.5    | 5.5  | 6.5  | V        |
| I <sub>GES</sub>          | Gate leakage current                 | V <sub>GE</sub> = V <sub>GE</sub> S, V <sub>CE</sub> = 0V, T <sub>j</sub> = 25°C            | —      | —    | 0.5  | μA       |
| V <sub>CE(sat)</sub>      | Collector-emitter saturation voltage | I <sub>C</sub> = 800A, V <sub>GE</sub> = 15V, T <sub>j</sub> = 25°C (Note 4)                | —      | 2.60 | 3.30 | V        |
|                           |                                      | I <sub>C</sub> = 800A, V <sub>GE</sub> = 15V, T <sub>j</sub> = 125°C (Note 4)               | —      | 3.10 | —    |          |
| C <sub>ies</sub>          | Input capacitance                    | V <sub>CE</sub> = 10V, f = 100kHz<br>V <sub>GE</sub> = 0V, T <sub>j</sub> = 25°C            | —      | 72   | —    | nF       |
| C <sub>oes</sub>          | Output capacitance                   |   | —      | 9.0  | —    | nF       |
| C <sub>res</sub>          | Reverse transfer capacitance         |   | —      | 3.6  | —    | nF       |
| Q <sub>g</sub>            | Total gate charge                    | V <sub>CC</sub> = 850V, I <sub>C</sub> = 800A, V <sub>GE</sub> = 15V, T <sub>j</sub> = 25°C | —      | 6.6  | —    | μC       |
| V <sub>EC</sub> (Note 2)  | Emitter-collector voltage            | I <sub>E</sub> = 800A, V <sub>GE</sub> = 0V, T <sub>j</sub> = 25°C (Note 4)                 | —      | 2.30 | 3.00 | V        |
|                           |                                      | I <sub>E</sub> = 800A, V <sub>GE</sub> = 0V, T <sub>j</sub> = 125°C (Note 4)                | —      | 2.00 | —    |          |
| t <sub>d(on)</sub>        | Turn-on delay time                   | V <sub>CC</sub> = 850V, I <sub>C</sub> = 800A, V <sub>GE</sub> = ±15V                       | —      | —    | 1.60 | μs       |
| t <sub>r</sub>            | Turn-on rise time                    | R <sub>G(on)</sub> = 3.3Ω, T <sub>j</sub> = 125°C, L <sub>s</sub> = 150nH                   | —      | —    | 1.30 | μs       |
| E <sub>on</sub>           | Turn-on switching energy             | Inductive load  | —      | 350  | —    | mJ/pulse |
| t <sub>d(off)</sub>       | Turn-off delay time                  | V <sub>CC</sub> = 850V, I <sub>C</sub> = 800A, V <sub>GE</sub> = ±15V                       | —      | —    | 2.70 | μs       |
| t <sub>f</sub>            | Turn-off fall time                   | R <sub>G(off)</sub> = 3.3Ω, T <sub>j</sub> = 125°C, L <sub>s</sub> = 150nH                  | —      | —    | 0.50 | μs       |
| E <sub>off</sub>          | Turn-off switching energy            | Inductive load  | —      | 260  | —    | mJ/pulse |
| t <sub>rr</sub> (Note 2)  | Reverse recovery time                | V <sub>CC</sub> = 850V, I <sub>C</sub> = 800A, V <sub>GE</sub> = ±15V                       | —      | —    | 2.70 | μs       |
| Q <sub>rr</sub> (Note 2)  | Reverse recovery charge              | R <sub>G(on)</sub> = 3.3Ω, T <sub>j</sub> = 125°C, L <sub>s</sub> = 150nH                   | —      | 300  | —    | μC       |
| E <sub>rec</sub> (Note 2) | Reverse recovery energy              | Inductive load  | —      | 120  | —    | mJ/pulse |

- Note 1. Pulse width and repetition rate should be such that junction temperature (T<sub>j</sub>) does not exceed T<sub>opmax</sub> rating (125°C).  
 2. The symbols represent characteristics of the anti-parallel, emitter to collector free-wheel diode (FWDi).  
 3. Junction temperature (T<sub>j</sub>) should not exceed T<sub>jmax</sub> rating (150°C).  
 4. Pulse width and repetition rate should be such as to cause negligible temperature rise.



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**THERMAL CHARACTERISTICS**

| Symbol                | Item                       | Conditions  | Limits |      |      | Unit |
|-----------------------|----------------------------|---|--------|------|------|------|
|                       |                            |   | Min    | Typ  | Max  |      |
| R <sub>th(j-c)Q</sub> | Thermal resistance         | Junction to Case, IGBT part, 1/2 module                     | —      | —    | 20.0 | K/kW |
| R <sub>th(j-c)R</sub> |                            | Junction to Case, FWDi part, 1/2 module                     | —      | —    | 34.0 | K/kW |
| R <sub>th(c-f)</sub>  | Contact thermal resistance | Case to Fin, $\lambda_{grease} = 1W/m \cdot K$ , 1/2 module | —      | 16.0 | —    | K/kW |

**MECHANICAL CHARACTERISTICS**

| Symbol         | Item                            | Conditions                     | Limits |      |      | Unit |
|----------------|---------------------------------|--------------------------------|--------|------|------|------|
|                |                                 |                                | Min    | Typ  | Max  |      |
| M              | Mounting torque                 | M8 : Main terminals screw      | 7.0    | —    | 13.0 | N·m  |
|                |                                 | M6 : Mounting screw            | 3.0    | —    | 6.0  |      |
|                |                                 | M4 : Auxiliary terminals screw | 1.0    | —    | 2.0  |      |
| —              | Mass                            |                                | —      | 1.0  | —    | kg   |
| CTI            | Comparative tracking index      |                                | 250    | —    | —    | —    |
| d <sub>a</sub> | Clearance distance in air       |                                | 10.0   | —    | —    | mm   |
| d <sub>s</sub> | Creepage distance along surface |                                | 15.0   | —    | —    | mm   |
| LC-E(int)      | Internal inductance             | IGBT part                      | —      | 18   | —    | nH   |
| RC-E(int)      | Internal lead resistance        | T <sub>C</sub> = 25°C          | —      | 0.16 | —    | mΩ   |

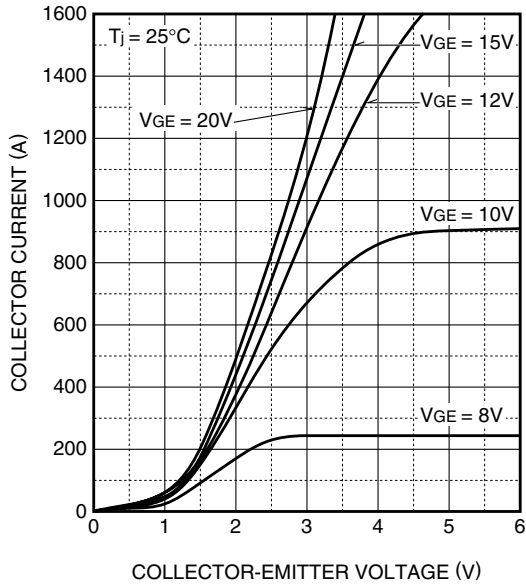
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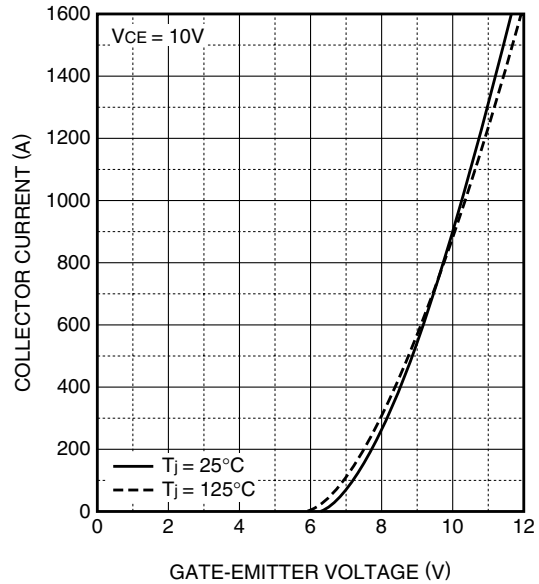
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**PERFORMANCE CURVES**

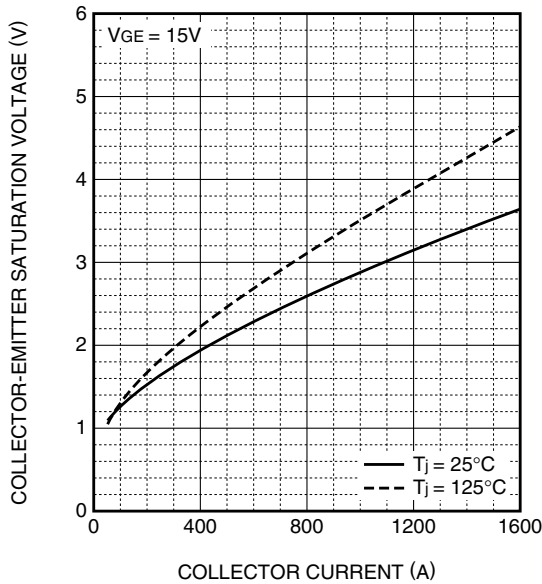
**OUTPUT CHARACTERISTICS  
(TYPICAL)**



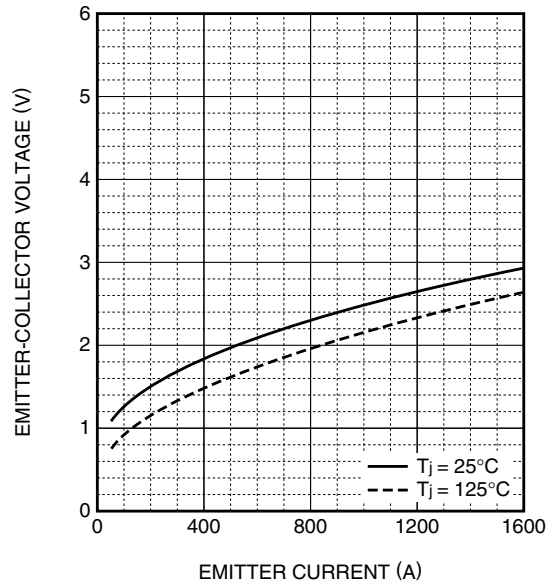
**TRANSFER CHARACTERISTICS  
(TYPICAL)**



**COLLECTOR-EMITTER SATURATION  
VOLTAGE CHARACTERISTICS  
(TYPICAL)**



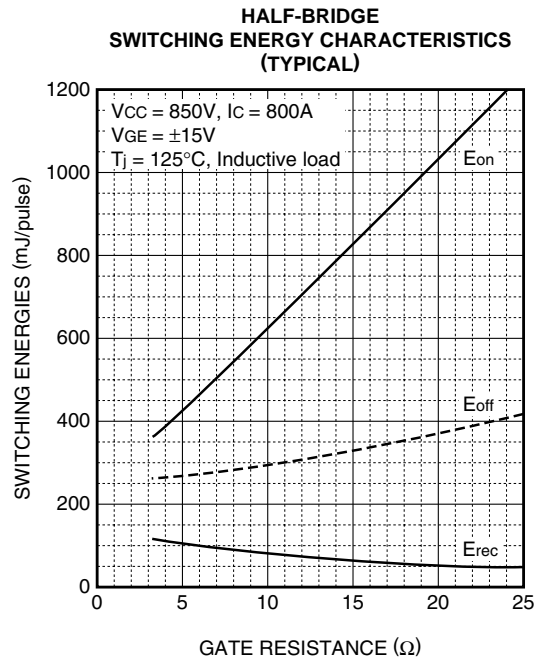
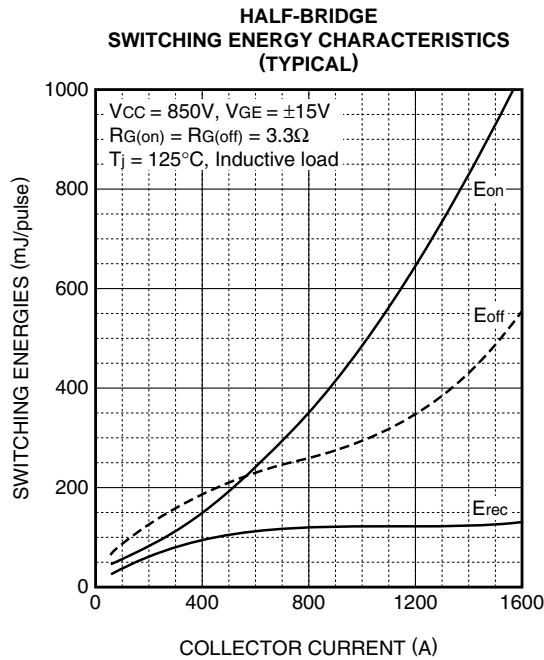
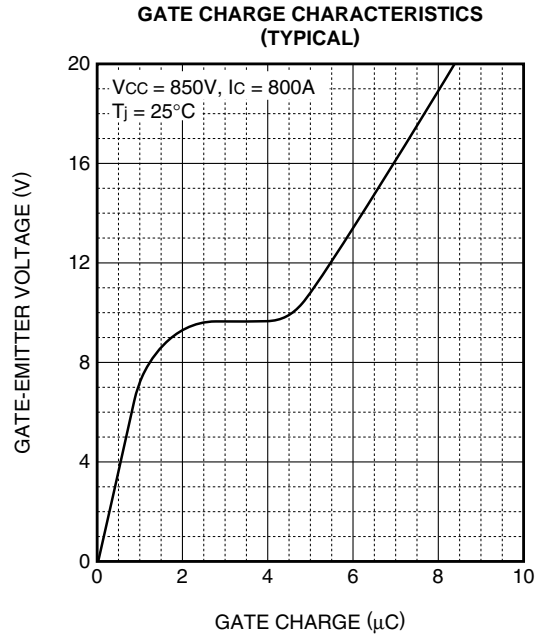
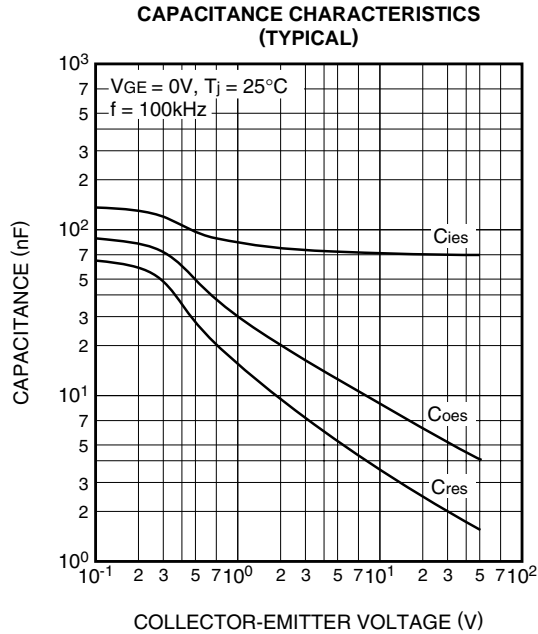
**FREE-WHEEL DIODE  
FORWARD CHARACTERISTICS  
(TYPICAL)**



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